

a contact portion for electrical connection to the TFT is disposed at a part of the pixel electrode; and

an insulating layer is embedded in a recess portion provided at the contact portion,
wherein the insulating layer is a light absorbing layer.

2. (Amended) An electrooptical device comprising a pixel matrix circuit constituted by a plurality of pixels each including at least one TFT and a pixel electrode connected to the TFT, wherein:

the pixel electrode includes a lamination structure of a first metal layer and a second metal layer; and

But Demand. an insulating layer is put between the first metal layer and the second metal layer at a contact portion where the first metal layer is connected with the TFT,

wherein the insulating layer is a light absorbing layer.

3. (Amended) An electrooptical device comprising a pixel matrix circuit constituted by a plurality of pixels each including at least one TFT and a pixel electrode connected to the TFT, wherein:

the pixel electrode includes a lamination structure of a first metal layer and a second metal layer;

an insulating film is embedded in a recess portion disposed on the first metal layer; and

the second metal layer is disposed so as to cover the first metal layer and the insulating film,

wherein the insulating layer is a light absorbing layer.

Cancel Claim 7.

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16. (Amended) An electronic device having at least one active matrix type liquid crystal panel, said liquid crystal panel comprising:

a substrate having an insulating surface;

an active matrix circuit formed over said substrate comprising a plurality of pixel electrodes, a plurality of switching elements for switching said pixel electrodes, respectively, an interlayer insulating film formed over said plurality of switching elements wherein each of said plurality of pixel electrodes is formed on said interlayer insulating film and electrically connected to the respective [pixel electrode] switching element through a contact hole of said interlayer insulating film; and

a driving circuit comprising a plurality of thin film transistors formed over said substrate for driving said active matrix circuit,

wherein a depression of said pixel electrode formed over said contact hole is filled with a[n] light absorbing insulating material.

Cancel Claims 32-33.

Please add the following new claims:

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--38. The electrooptical device according to claim 1 wherein said light absorbing layer comprises a resin in which a pigment or a carbon-based material is dispersed.--

--39. The electrooptical device according to claim 2 wherein said light absorbing layer comprises a resin in which a pigment or a carbon-based material is dispersed.--

--40. The electrooptical device according to claim 3 wherein said light absorbing layer comprises a resin in which a pigment or a carbon-based material is dispersed.--

--41. The electronic device according to claim 16 wherein said light absorbing insulating material comprises a resin in which a pigment or a carbon-based material is dispersed.--

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--42. An electronic device having at least one active matrix type display device comprising:
at least one switching element;
at least one interlayer insulating film formed over said switching element;
a pixel electrode formed on said interlayer insulating film and electrically connected to said switching element through a contact hole of said interlayer insulating film;
a light absorbing insulating material formed in a depression of said pixel electrode over said contact hole.--

--43. The electronic device according to claim 42 wherein an upper surface of said pixel electrode is substantially flush with said light absorbing insulating material.--

--44. The electronic device according to claim 42 wherein said switching element is a thin film transistor.--

--45. The electronic device according to claim 42 wherein said switching element is a MOSFET.--

--46. The electronic device according to claim 42 wherein said light absorbing insulating material comprises a resin and a pigment.--

--47. The electronic device according to claim 42 wherein said light absorbing insulating material comprises a resin and a carbon-based material.--

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--48. An electronic device having at least one active matrix type display device comprising:

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at least one switching element;
at least one interlayer insulating film formed over said switching element;
a pixel electrode formed on said interlayer insulating film and electrically connected to said switching element through a contact hole of said interlayer insulating film;
a light absorbing insulating material formed in a depression of said pixel electrode over said contact hole,
wherein said insulating material contains a carbon-based material.--

--49. The electronic device according to claim 48 wherein an upper surface of said pixel electrode is substantially flush with said light absorbing insulating material.--

--50. The electronic device according to claim 48 wherein said switching element is a thin film transistor.--

--51. The electronic device according to claim 48 wherein said switching element is a MOSFET--

--52. The electronic device according to claim 48 further comprising a conductive layer formed on said pixel electrode and said insulating material.--

--53. The electronic device according to claim 42 further comprising a conductive layer formed on said pixel electrode and said light absorbing insulating material.--

--54. The electronic device according to claim 42 wherein said interlayer insulating film comprises an organic resin.--

B³ --55. An electronic device according to claim 42 wherein said device is a portable telephone.--

--56. An electronic device according to claim 42 wherein said device is a video camera.--

--57. An electronic device according to claim 42 wherein said device is a mobile computer.--

--58. An electronic device according to claim 42 wherein said device is a rear projector.--

--59. An electronic device according to claim 42 wherein said device is a front projector.--

--60. The electronic device according to claim 48 wherein said interlayer insulating film comprises an organic resin.--